



# Bipolar NPN Bare Die – BTN6050

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## Part Description

The BTN6050 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 170V
- VCEO = 60V
- VEBO = 6V
- hFE = 160-440 @ VCE = 2V, IC = 0.1A
- VCE(Sat) = 0.35V @ IC = 2A, IB = 50mA
- fT = 200 MHz @ VCE = 5V, IE = 0A
- COBO = 20pF @ VCB = 10V

## Features

Low VCE(sat)

## Die Size (Unawn)

1200µm X 1200µm, 47 Mils X 47 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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